



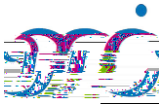
DGW75N65CTH2A



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Electrical Characteristics of the IGBT $T_j=25$ unless otherwise specified

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C$	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.75mA$	3.2	4.0	4.8	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=75A$ $T_j=25^\circ C,$ $T_j=125^\circ C$ $T_j=150^\circ C$	1.20	1.65 1.95 2.05	2.10	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=650V, V_{GE}=0V$ $T_j=25^\circ C,$ $T_j=150^\circ C$			0.25 3.00	



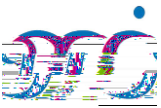
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Electrical Characteristics of the DIODE

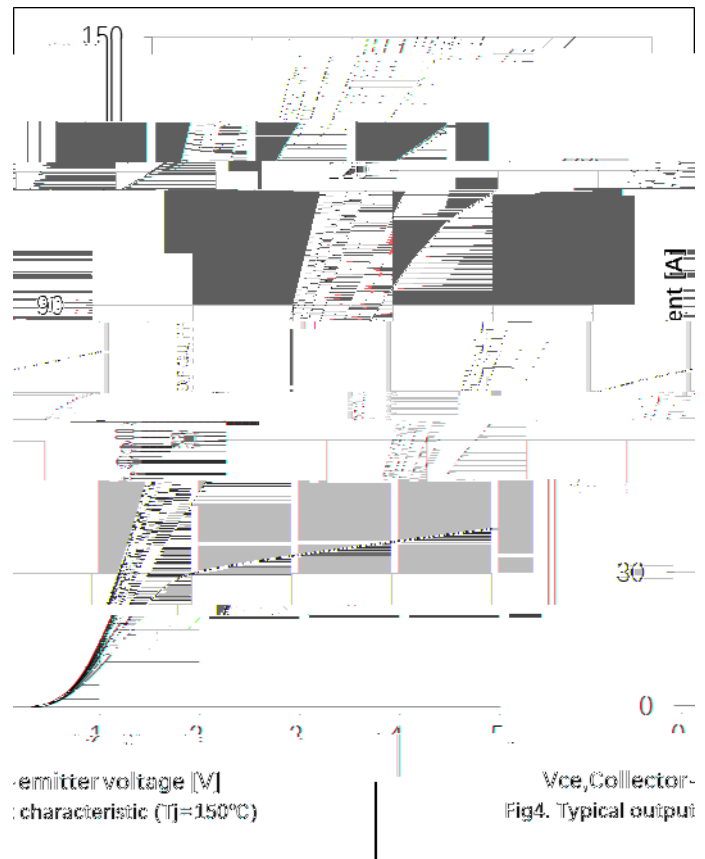
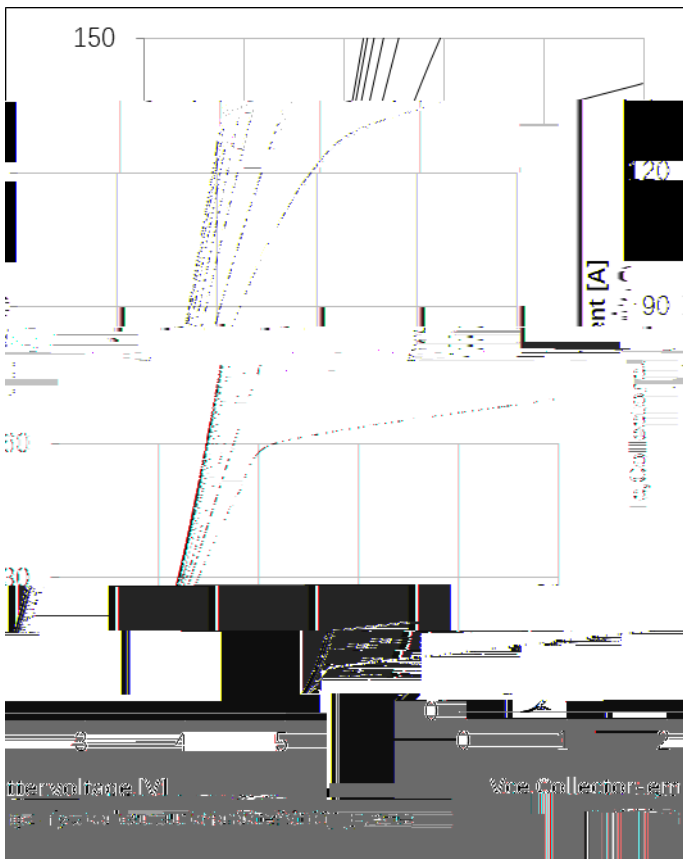
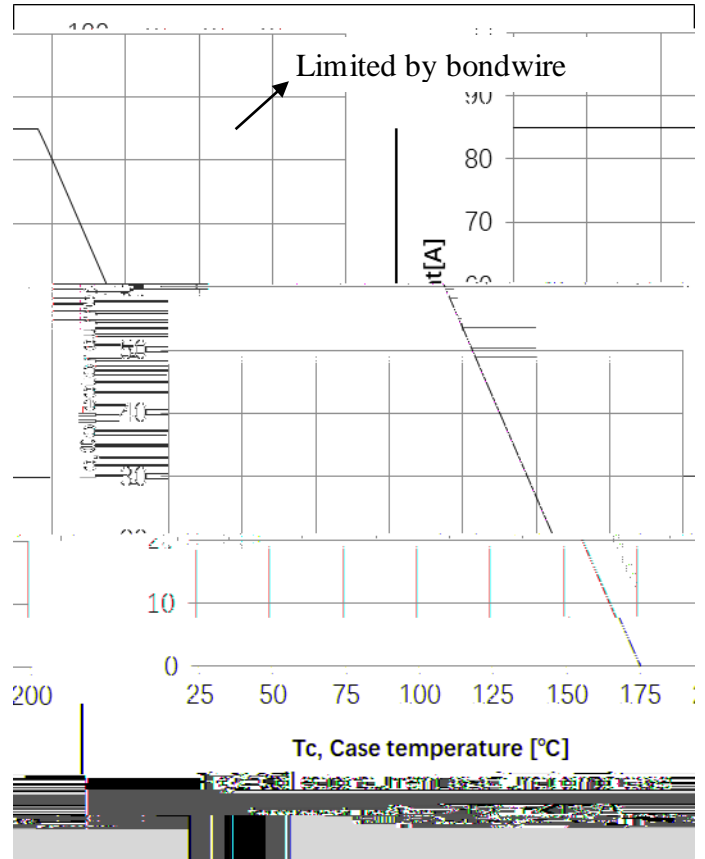
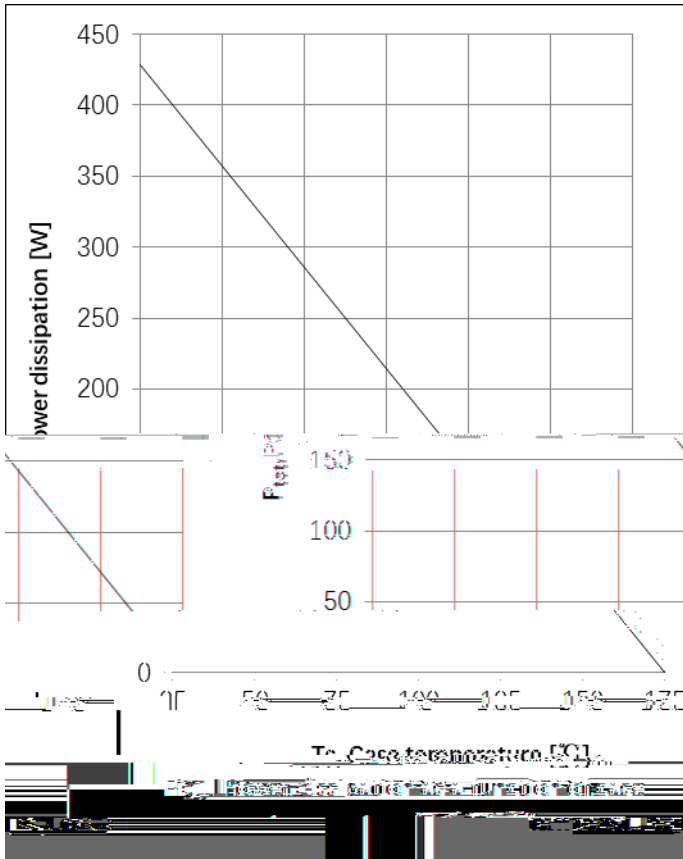
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at $T_j=25$						
Reverse Recovery Current	I_{rr}		-	10	-	A

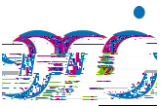
Reverse Recovery Charge

$I_F=75A, V_R=400V$
 $-di/dt=440$



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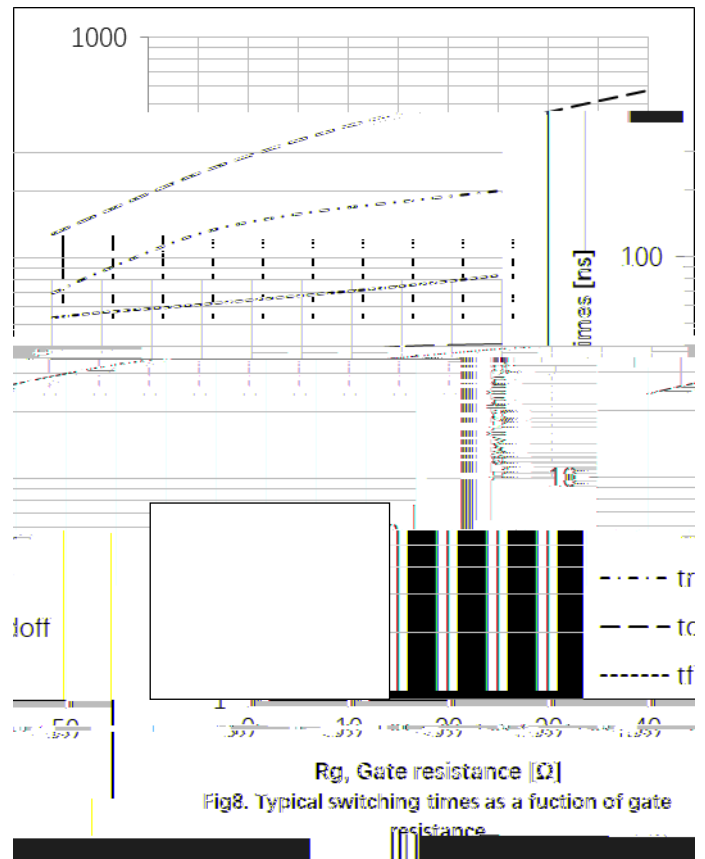
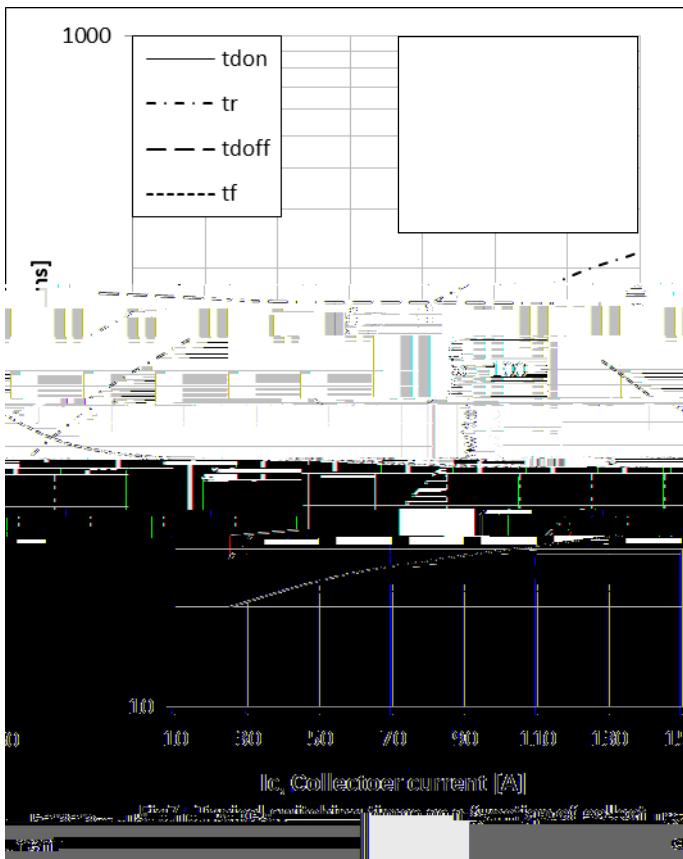
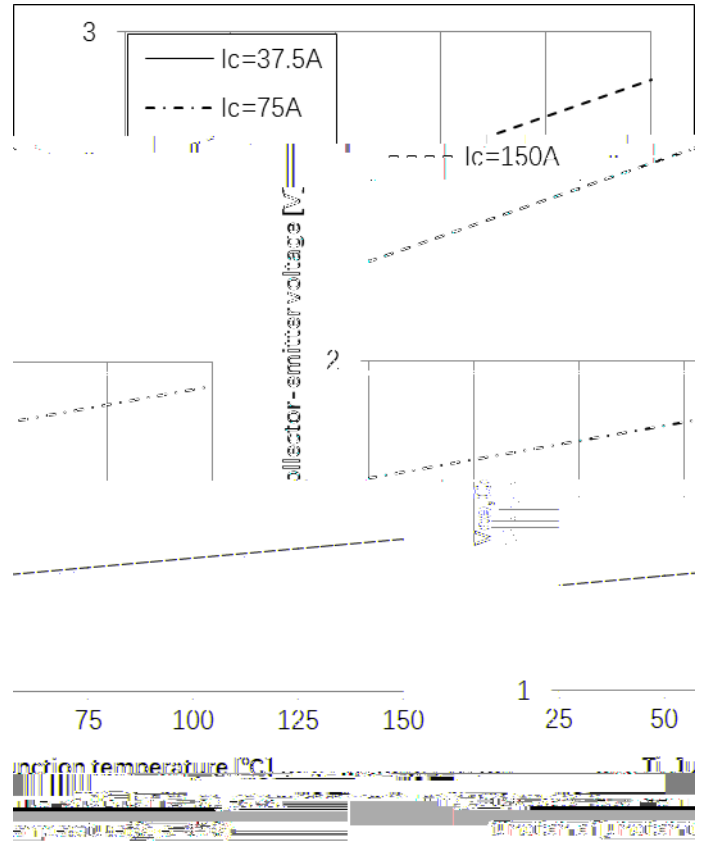
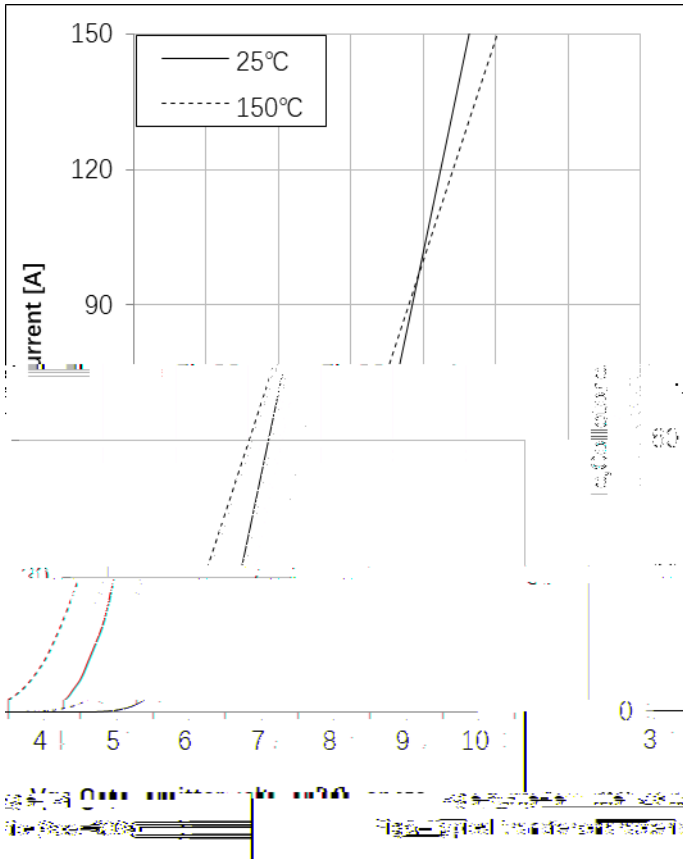
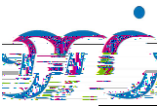
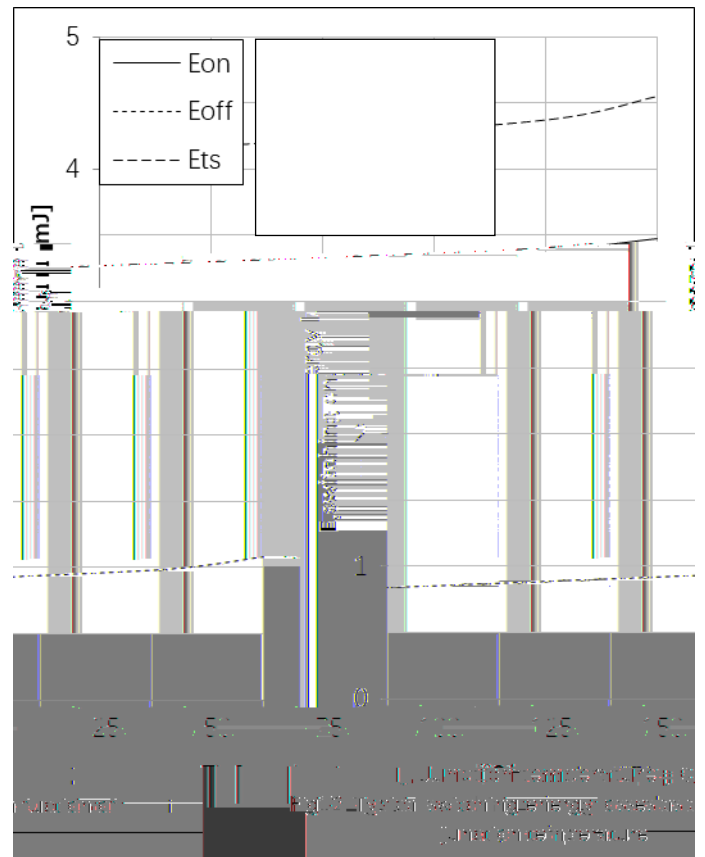
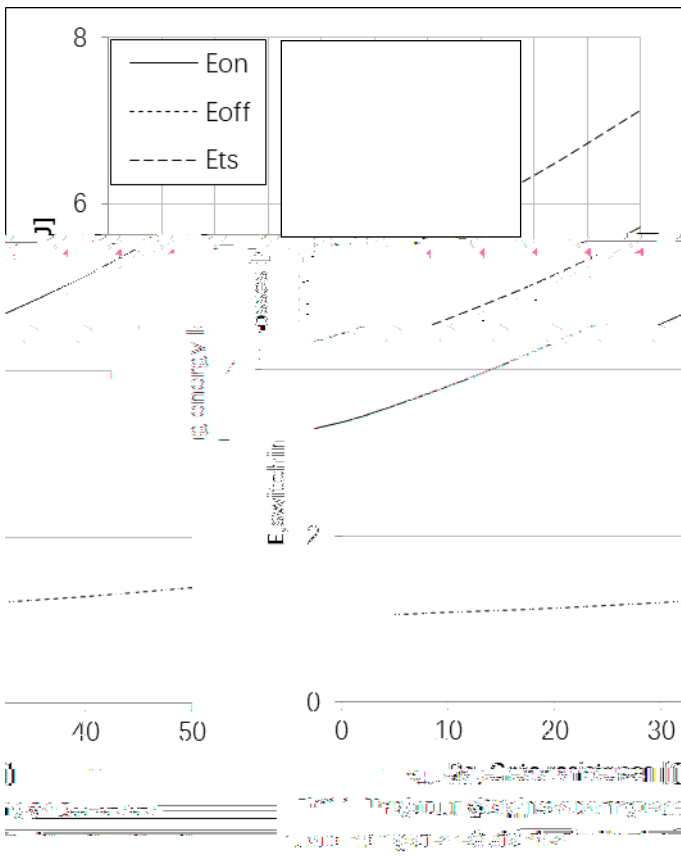
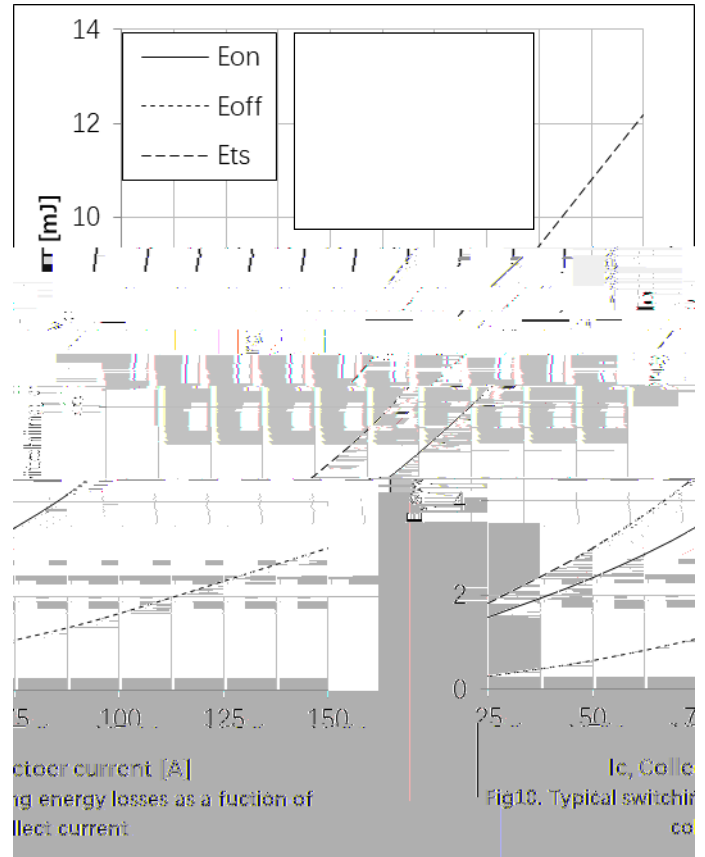
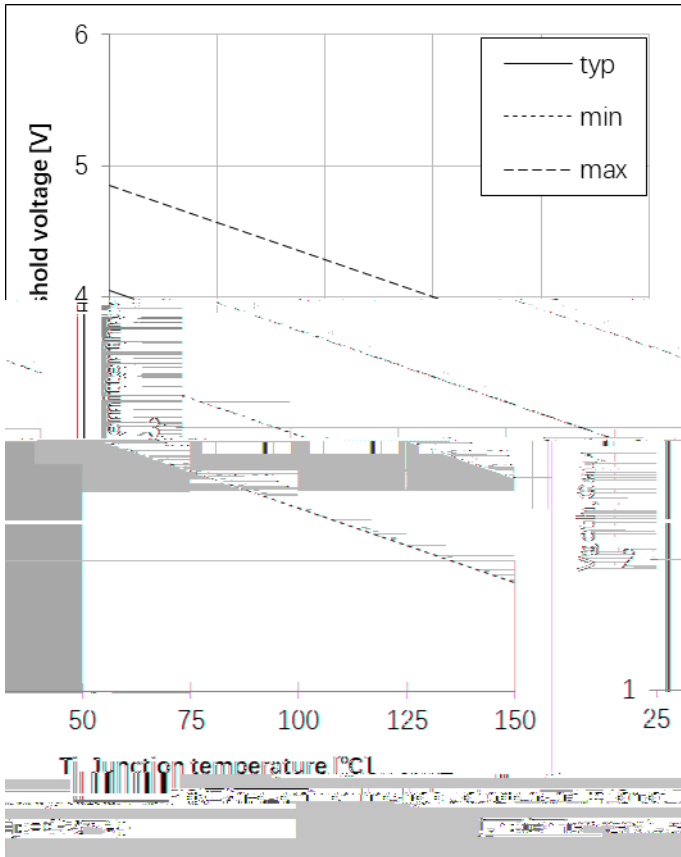


Fig8. Typical switching times as a function of gate resistance

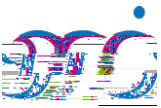


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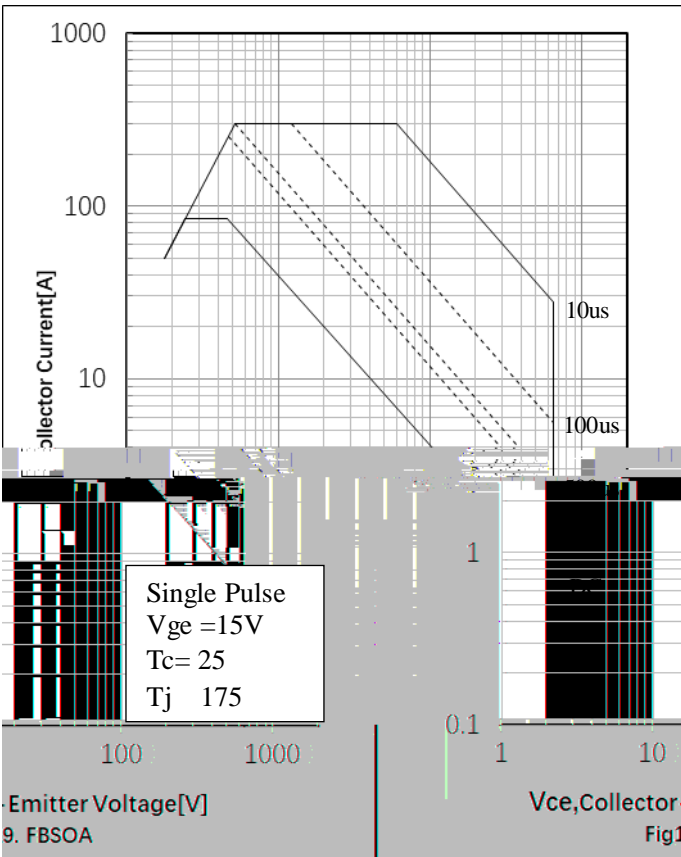
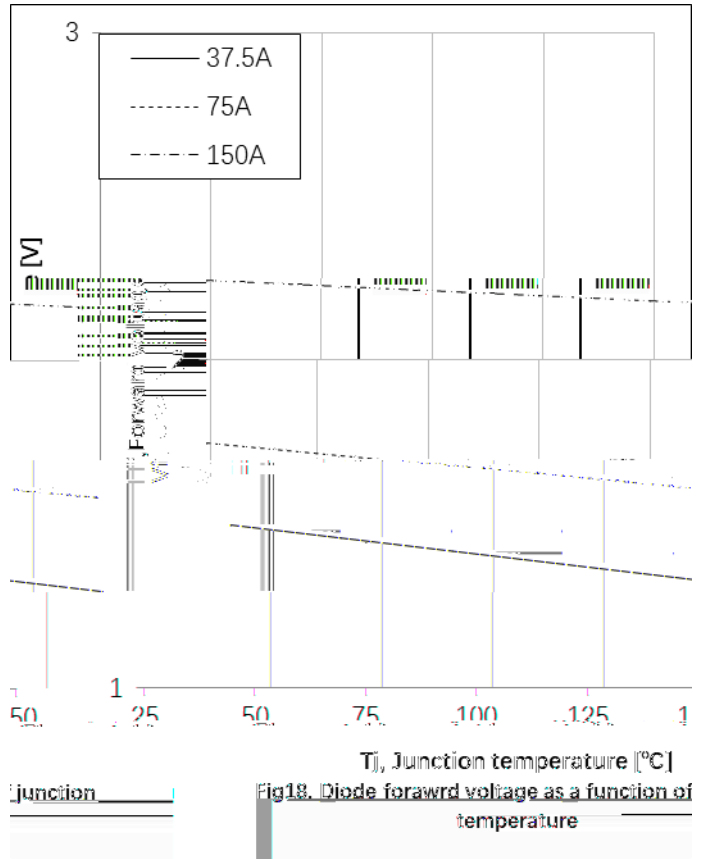
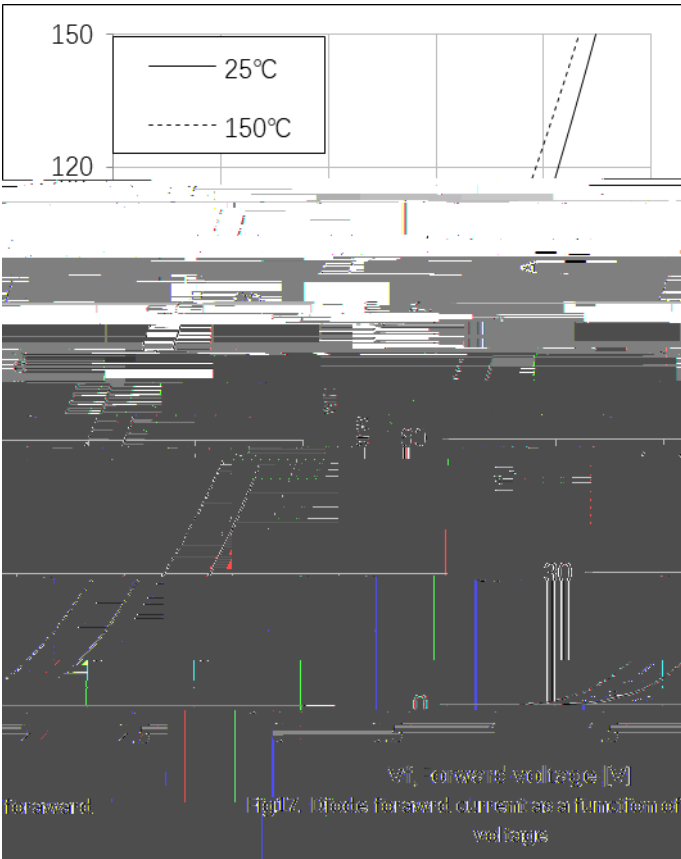




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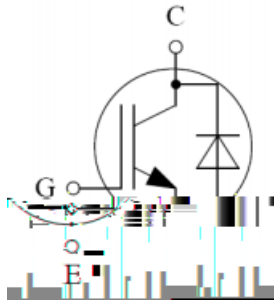


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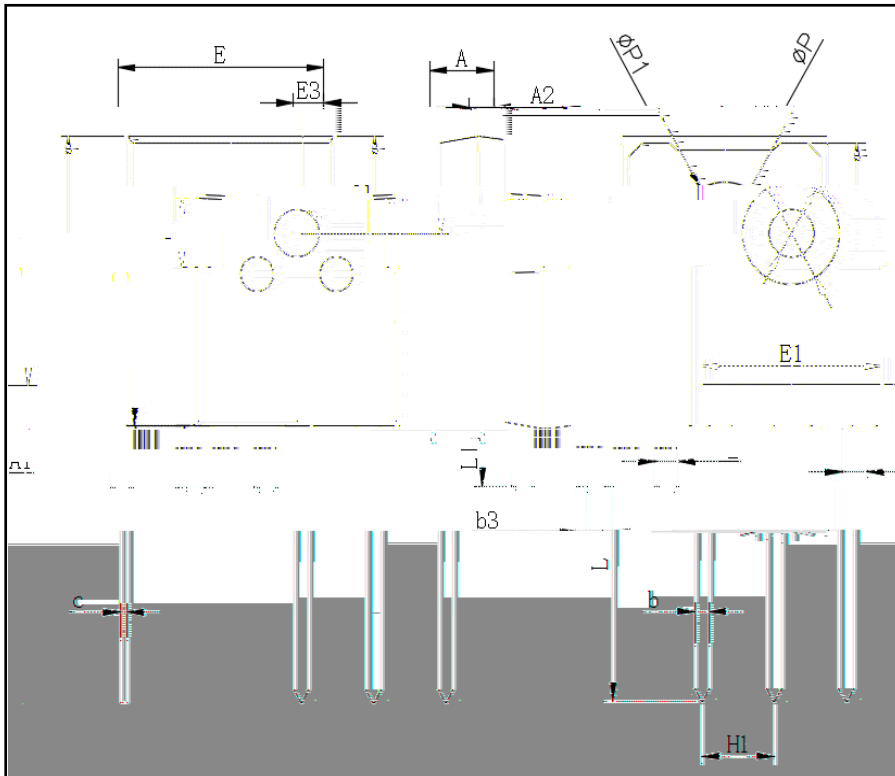




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Package Outline Information



TO-247AB		
Dim	Min	Max
A	4.80	5.20
A1	2.21	2.61
A2	1.85	2.15
b	1.0	1.4
b2	1.91	2.21
C	0.5	0.7
D	20.70	21.30
D1	16.25	16.85
E	15.50	16.10
E1	13.0	13.6
E2	4.80	5.20
E3	2.30	2.70
L	19.62	20.22
L1	-	4.30
P	3.40	3.80
P1	-	7.30
S	6.15TYP	
H1	5.44TYP	
b3	2.80	3.20